

In the Abstract:

Delete the existing Abstract and substitute the following in its place. No amended version of the Abstract is provided in any accompanying pages separate from this amendment in accordance with 37 CFR § 1.121(b)(1)(iii) as this is a replacement, not an amendment.

B2
A field effect transistor includes a pair of source/drain regions having a channel region positioned therebetween. A gate is positioned operatively proximate the channel region. The gate includes semiconductive material conductively doped with at least one of a p-type or n-type conductivity enhancing impurity effective to render the semiconductive material electrically conductive, a silicide layer and a conductive diffusion barrier layer effective to restrict diffusion of p-type or n-type conductivity enhancing impurity. The conductive diffusion barrier layer includes TiW_xN_y . Integrated circuitry is also disclosed.

In the Specification

Please replace the paragraph beginning at line 8 of page 2 with the following clean replacement paragraph in accordance with 37 CFR § 1.121(b)(1)(ii). A marked-up version showing amendments to the